Chennupati Jagadish

List of Publications by Year
in descending order

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1,153 papers	23,843 citations	11608 70 h-index	22102 113 g-index
1187 all docs	1187 docs citations	1187 times ranked	16770 citing authors

#	Article	IF	Citations
1	Optically pumped room-temperature GaAs nanowire lasers. Nature Photonics, 2013, 7, 963-968.	15.6	503
2	Phase Perfection in Zinc Blende and Wurtzite IIIâˆ’V Nanowires Using Basic Growth Parameters. Nano Letters, 2010, 10, 908-915.	4.5	443
3	Broadband Metamaterial Absorbers. Advanced Optical Materials, 2019, 7, 1800995.	3.6	404
4	Twin-Free Uniform Epitaxial GaAs Nanowires Grown by a Two-Temperature Process. Nano Letters, 2007, 7, 921-926.	4.5	297
5	Investigation of Pt/Ti bilayer metallization on silicon for ferroelectric thin film integration. Journal of Applied Physics, 1994, 75, 232-239.	1.1	267
6	Electronic properties of GaAs, InAs and InP nanowires studied by terahertz spectroscopy. Nanotechnology, 2013, 24, 214006.	1.3	264
7	IIIâ€“V semiconductor nanowires for optoelectronic device applications. Progress in Quantum Electronics, 2011, 35, 23-75.	3.5	256
8	Effects of interdiffusion on the luminescence of InGaAs/GaAs quantum dots. Applied Physics Letters, 1996, 69, 1888-1890.	1.5	253
9	Carrier Lifetime and Mobility Enhancement in Nearly Defect-Free Coreâˆ’Shell Nanowires Measured Using Time-Resolved Terahertz Spectroscopy. Nano Letters, 2009, 9, 3349-3353.	4.5	253
10	Review of zincblende ZnO: Stability of metastable ZnO phases. Journal of Applied Physics, 2007, 102, .	1.1	246
11	Ion-beam-produced structural defects in ZnO. Physical Review B, 2003, 67, .	1.1	244
12	Mechanical deformation of single-crystal ZnO. Applied Physics Letters, 2002, 80, 956-958.	1.5	239
13	Nonlinear Generation of Vector Beams From AlGaAs Nanoantennas. Nano Letters, 2016, 16, 7191-7197.	4.5	237
14	Influence of Nanowire Density on the Shape and Optical Properties of Ternary InGaAs Nanowires. Nano Letters, 2006, 6, 599-604.	4.5	222
15	Identifying carbon as the source of visible single-photon emission from hexagonal boron nitride. Nature Materials, 2021, 20, 321-328.	13.3	210
16	Selective-Area Epitaxy of Pure Wurtzite InP Nanowires: High Quantum Efficiency and Room-Temperature Lasing. Nano Letters, 2014, 14, 5206-5211.	4.5	198
17	Polarization and temperature dependence of photoluminescence from zincblende and wurtzite InP nanowires. Applied Physics Letters, 2007, 91, .	1.5	196
18	Transient Terahertz Conductivity of GaAs Nanowires. Nano Letters, 2007, 7, 2162-2165.	4.5	194

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19	III-V compound SC for optoelectronic devices. Materials Today, 2009, 12, 22-32.	8.3	194
20	Damage buildup in GaN under ion bombardment. Physical Review B, 2000, 62, 7510-7522.	1.1	170
21	Carrier Dynamics and Quantum Confinement in type II ZB-WZ InP Nanowire Homostructures. Nano Letters, 2009, 9, 648-654.	4.5	168
22	Electro-optical switching by liquid-crystal controlled metasurfaces. Optics Express, 2013, 21, 8879.	1.7	163
23	Design and fabrication of silicon nanowires towards efficient solar cells. Nano Today, 2016, 11, 704-737.	6.2	163
24	Nanoindentation of epitaxial GaN films. Applied Physics Letters, 2000, 77, 3373-3375.	1.5	161
25	Temperature dependence of photoluminescence from single core-shell GaAsâ€“AlGaAs nanowires. Applied Physics Letters, 2006, 89, 173126.	1.5	158
26	Ultralow Surface Recombination Velocity in InP Nanowires Probed by Terahertz Spectroscopy. Nano Letters, 2012, 12, 5325-5330.	4.5	158
27	Growth Mechanism of Truncated Triangular IIIâ€“V Nanowires. Small, 2007, 3, 389-393.	5.2	136
28	Liquid crystal based nonlinear fishnet metamaterials. Applied Physics Letters, 2012, 100, .	1.5	128
29	Tantalum Oxide Electron-Selective Heterocontacts for Silicon Photovoltaics and Photoelectrochemical Water Reduction. ACS Energy Letters, 2018, 3, 125-131.	8.8	127
30	Unexpected Benefits of Rapid Growth Rate for IIIâ^'V Nanowires. Nano Letters, 2009, 9, 695-701.	4.5	126
31	Multipulse operation of a Ti:sapphire laser mode locked by an ion-implanted semiconductor saturable-absorber mirror. Journal of the Optical Society of America B: Optical Physics, 1999, 16, 895.	0.9	122
32	Polarization-sensitive terahertz detection by multicontact photoconductive receivers. Applied Physics Letters, 2005, 86, 254102.	1.5	120
33	Basic Properties and Applications of ZnO. , 2006, , 1-20.		116
34	Super Deformability and Youngâ€™s Modulus of GaAs Nanowires. Advanced Materials, 2011, 23, 1356-1360.	11.1	114
35	Effect of ion species on the accumulation of ion-beam damage inGaN. Physical Review B, 2001, 64, .	1.1	112
36	Nearly intrinsic exciton lifetimes in single twin-free GaAsâ^•AlGaAs core-shell nanowire heterostructures. Applied Physics Letters, 2008, 93, .	1.5	109

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37	Atomically thin optical lenses and gratings. Light: Science and Applications, 2016, 5, e16046-e16046.	7.7	107
38	Optical, Structural, and Numerical Investigations of GaAs/AlGaAs Coreâ€“Multishell Nanowire Quantum Well Tubes. Nano Letters, 2013, 13, 1016-1022.	4.5	106
39	Single Nanowire Photoconductive Terahertz Detectors. Nano Letters, 2015, 15, 206-210.	4.5	105
40	Chemical origin of the yellow luminescence in GaN. Journal of Applied Physics, 2002, 91, 5867-5874.	1.1	103
41	Influence of surface passivation on ultrafast carrier dynamics and terahertz radiation generation in GaAs. Applied Physics Letters, 2006, 89, 232102.	1.5	103
42	Direct Measure of Strain and Electronic Structure in GaAs/GaP Coreâ˜Shell Nanowires. Nano Letters, 2010, 10, 880-886.	4.5	101
43	Nonlinear Optical Magnetism Revealed by Second-Harmonic Generation in Nanoantennas. Nano Letters, 2017, 17, 3914-3918.	4.5	100
44	Structural characteristics of GaSbâ•GaAs nanowire heterostructures grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 231917.	1.5	99
45	The effect of V/III ratio and catalyst particle size on the crystal structure and optical properties of InP nanowires. Nanotechnology, 2009, 20, 225606.	1.3	99
46	Removal of Surface States and Recovery of Band-Edge Emission in InAs Nanowires through Surface Passivation. Nano Letters, 2012, 12, 3378-3384.	4.5	98
47	High Purity GaAs Nanowires Free of Planar Defects: Growth and Characterization. Advanced Functional Materials, 2008, 18, 3794-3800.	7.8	97
48	Enhanced Minority Carrier Lifetimes in GaAs/AlGaAs Coreâ€“Shell Nanowires through Shell Growth Optimization. Nano Letters, 2013, 13, 5135-5140.	4.5	97
49	Thermal stability of ion-implanted hydrogen in ZnO. Applied Physics Letters, 2002, 81, 3996-3998.	1.5	96
50	Novel Growth Phenomena Observed in Axial InAs/GaAs Nanowire Heterostructures. Small, 2007, 3, 1873-1877.	5.2	93
51	Nucleation Transitions for InGaAs Islands on Vicinal (100) GaAs. Physical Review Letters, 1997, 78, 4942-4945.	2.9	92
52	Generation of vacancy-type point defects in single collision cascades during swift-ion bombardment of silicon. Physical Review B, 1997, 55, 10498-10507.	1.1	92
53	Contact-induced defect propagation in ZnO. Applied Physics Letters, 2002, 80, 4537-4539.	1.5	90
54	Nature of heterointerfaces in GaAs/InAs and InAs/GaAs axial nanowire heterostructures. Applied Physics Letters, 2008, 93, .	1.5	90

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55	Crystalline-to-amorphous transition for Si-ion irradiation of Si(100). Physical Review B, 1991, 44, 9118-9121.	1.1	86
56	Large energy shifts in GaAsâ€AlGaAs quantum wells by proton irradiationâ€induced intermixing. Applied Physics Letters, 1996, 68, 2401-2403.	1.5	86
57	Annealing kinetics of vacancy-related defects in low-dose MeV self-ion-implantedn-type silicon. Physical Review B, 2001, 64, .	1.1	85
58	Nonlinear Absorption Applications of CH₃NH₃PbBr₃ Perovskite Crystals. Advanced Functional Materials, 2018, 28, 1707175.	7.8	84
59	Lattice damage produced in GaN by swift heavy ions. Journal of Applied Physics, 2004, 95, 5360-5365.	1.1	82
60	Three-dimensional cross-nanowire networks recover full terahertz state. Science, 2020, 368, 510-513.	6.0	81
61	Long minority carrier lifetime in Au-catalyzed GaAs/AlxGa1â^'xAs core-shell nanowires. Applied Physics Letters, 2012, 101, .	1.5	80
62	Polarity-Driven 3-Fold Symmetry of GaAs/AlGaAs Core Multishell Nanowires. Nano Letters, 2013, 13, 3742-3748.	4.5	80
63	Design and Room-Temperature Operation of GaAs/AlGaAs Multiple Quantum Well Nanowire Lasers. Nano Letters, 2016, 16, 5080-5086.	4.5	80
64	Characterization of Semiconductor Nanowires Using Optical Tweezers. Nano Letters, 2011, 11, 2375-2381.	4.5	79
65	Phase Separation Induced by Au Catalysts in Ternary InGaAs Nanowires. Nano Letters, 2013, 13, 643-650.	4.5	79
66	Electron Mobilities Approaching Bulk Limits in â€œSurface-Freeâ€•GaAs Nanowires. Nano Letters, 2014, 14, 5989-5994.	4.5	79
67	Twinning Superlattice Formation in GaAs Nanowires. ACS Nano, 2013, 7, 8105-8114.	7.3	77
68	An Ultrafast Switchable Terahertz Polarization Modulator Based on IIIâ€“V Semiconductor Nanowires. Nano Letters, 2017, 17, 2603-2610.	4.5	77
69	Picosecond carrier lifetime in GaAs implanted with high doses of As ions: An alternative material to lowâ€temperature GaAs for optoelectronic applications. Applied Physics Letters, 1995, 66, 3304-3306.	1.5	76
70	IIIâ€“V Semiconductor Single Nanowire Solar Cells: A Review. Advanced Materials Technologies, 2018, 3, 1800005.	3.0	75
71	Selective area epitaxy of IIIâ€“V nanostructure arrays and networks: Growth, applications, and future directions. Applied Physics Reviews, 2021, 8, .	5.5	75
72	Mode Profiling of Semiconductor Nanowire Lasers. Nano Letters, 2015, 15, 5342-5348.	4.5	73

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73	Ion-beam-induced dissociation and bubble formation in GaN. Applied Physics Letters, 2000, 77, 3577-3579.	1.5	72
74	Ion-beam-induced porosity of GaN. Applied Physics Letters, 2000, 77, 1455-1457.	1.5	71
75	Tunable Polarity in a IIIâ€“V Nanowire by Droplet Wetting and Surface Energy Engineering. Advanced Materials, 2015, 27, 6096-6103.	11.1	69
76	The influence of pearlite on Barkhausen noise generation in plain carbon steels. Acta Metallurgica Et Materialia, 1991, 39, 1555-1562.	1.9	68
77	Mechanical properties of ZnO epitaxial layers grown on a- and c-axis sapphire. Applied Physics Letters, 2005, 86, 203105.	1.5	68
78	Doping-enhanced radiative efficiency enables lasing in unpassivated GaAs nanowires. Nature Communications, 2016, 7, 11927.	5.8	68
79	Excited State Biexcitons in Atomically Thin MoSe₂. ACS Nano, 2017, 11, 7468-7475.	7.3	68
80	Implant isolation of ZnO. Journal of Applied Physics, 2003, 93, 2972-2976.	1.1	66
81	Distinct Photocurrent Response of Individual GaAs Nanowires Induced by n-Type Doping. ACS Nano, 2012, 6, 6005-6013.	7.3	66
82	Tailoring Second-Harmonic Emission from (111)-GaAs Nanoantennas. Nano Letters, 2019, 19, 3905-3911.	4.5	66
83	Ion damage buildup and amorphization processes in AlxGa1â^'xAs. Journal of Applied Physics, 1995, 77, 87-94.	1.1	65
84	Nonlinear frequency conversion in optical nanoantennas and metasurfaces: materials evolution and fabrication. Opto-Electronic Advances, 2018, 1, 18002101-18002112.	6.4	65
85	Electrical isolation of ZnO by ion bombardment. Applied Physics Letters, 2002, 81, 3350-3352.	1.5	64
86	Room temperature GaAsSb single nanowire infrared photodetectors. Nanotechnology, 2015, 26, 445202.	1.3	63
87	Defect-Free <110> Zinc-Blende Structured InAs Nanowires Catalyzed by Palladium. Nano Letters, 2012, 12, 5744-5749.	4.5	62
88	Generation of point defects in crystalline silicon by MeV heavy ions: Dose rate and temperature dependence. Physical Review Letters, 1993, 71, 1860-1863.	2.9	61
89	Effect of a High Density of Stacking Faults on the Youngâ€™s Modulus of GaAs Nanowires. Nano Letters, 2016, 16, 1911-1916.	4.5	61
90	Dual-channel spontaneous emission of quantum dots in magnetic metamaterials. Nature Communications, 2013, 4, 2949.	5.8	60

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91	Ion-beam-produced damage and its stability in AlN films. Journal of Applied Physics, 2002, 92, 3554-3558.	1.1	58
92	Carrier dynamics in ion-implanted GaAs studied by simulation and observation of terahertz emission. Physical Review B, 2004, 70, .	1.1	58
93	Nonlinear Optical Processes in Optically Trapped InP Nanowires. Nano Letters, 2011, 11, 4149-4153.	4.5	58
94	Efficiency enhancement of axial junction InP single nanowire solar cells by dielectric coating. Nano Energy, 2016, 28, 106-114.	8.2	58
95	Engineering Highly Interconnected Neuronal Networks on Nanowire Scaffolds. Nano Letters, 2017, 17, 3369-3375.	4.5	58
96	Over 17% Efficiency Standâ€Alone Solar Water Splitting Enabled by Perovskiteâ€Silicon Tandem Absorbers. Advanced Energy Materials, 2020, 10, 2000772.	10.2	58
97	Suppression of interdiffusion in InGaAs/GaAs quantum dots using dielectric layer of titanium dioxide. Applied Physics Letters, 2003, 82, 2613-2615.	1.5	57
98	Simultaneous Selective-Area and Vaporâ€“Liquidâ€“Solid Growth of InP Nanowire Arrays. Nano Letters, 2016, 16, 4361-4367.	4.5	57
99	Flow modulation epitaxy of hexagonal boron nitride. 2D Materials, 2018, 5, 045018.	2.0	57
100	Controlling the morphology, composition and crystal structure in gold-seeded GaAs_{1â^'x}Sb_xnanowires. Nanoscale, 2015, 7, 4995-5003.	2.8	56
101	Point defects in MeV ion-implanted silicon studied by deep level transient spectroscopy. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 183-190.	0.6	55
102	Ion-implanted In0.53Ga0.47As for ultrafast optoelectronic applications. Applied Physics Letters, 2003, 82, 3913-3915.	1.5	55
103	Origin of stress in radio frequency magnetron sputtered zinc oxide thin films. Journal of Applied Physics, 2011, 109, .	1.1	55
104	Integration of Semiconductor Nanowire Lasers with Polymeric Waveguide Devices on a Mechanically Flexible Substrate. Nano Letters, 2017, 17, 5990-5994.	4.5	55
105	Dynamic annealing in III-nitrides under ion bombardment. Journal of Applied Physics, 2004, 95, 3048-3054.	1.1	54
106	Electron-hole recombination properties of In0.5Ga0.5As/GaAs quantum dot solar cells and the influence on the open circuit voltage. Applied Physics Letters, 2010, 97, .	1.5	54
107	Strong Carrier Lifetime Enhancement in GaAs Nanowires Coated with Semiconducting Polymer. Nano Letters, 2012, 12, 6293-6301.	4.5	54
108	Magnetism of Co-doped ZnO epitaxially grown on a ZnO substrate. Physical Review B, 2012, 85, .	1.1	54

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109	IIIâ€“V Semiconductor Materials for Solar Hydrogen Production: Status and Prospects. ACS Energy Letters, 2020, 5, 611-622.	8.8	54
110	Influence of uniaxial elastic stress on power spectrum and pulse height distribution of surface Barkhausen noise in pipeline steel. IEEE Transactions on Magnetics, 1990, 26, 1160-1163.	1.2	53
111	Photoconductive response correction for detectors of terahertz radiation. Journal of Applied Physics, 2008, 104, .	1.1	53
112	Optical design of nanowire absorbers for wavelength selective photodetectors. Scientific Reports, 2015, 5, 15339.	1.6	53
113	Forward and Backward Switching of Nonlinear Unidirectional Emission from GaAs Nanoantennas. ACS Nano, 2020, 14, 1379-1389.	7.3	53
114	Electrical isolation of GaN by MeV ion irradiation. Applied Physics Letters, 2001, 78, 943-945.	1.5	52
115	Growth temperature and V/III ratio effects on the morphology and crystal structure of InP nanowires. Journal Physics D: Applied Physics, 2010, 43, 445402.	1.3	52
116	Understanding the True Shape of Au-Catalyzed GaAs Nanowires. Nano Letters, 2014, 14, 5865-5872.	4.5	52
117	Evolution of Epitaxial InAs Nanowires on GaAs (111)B. Small, 2009, 5, 366-369.	5.2	51
118	Nanowires Grown on InP (100): Growth Directions, Facets, Crystal Structures, and Relative Yield Control. ACS Nano, 2014, 8, 6945-6954.	7.3	51
119	Strong surface disorder and loss of N produced by ion bombardment of GaN. Applied Physics Letters, 2000, 76, 3899-3901.	1.5	50
120	InGaAs quantum dots grown with GaP strain compensation layers. Journal of Applied Physics, 2004, 95, 5710-5714.	1.1	50
121	Room temperature photocurrent spectroscopy of single zincblende and wurtzite InP nanowires. Applied Physics Letters, 2009, 94, 193115.	1.5	50
122	Structural, compositional and optical properties of PECVD silicon nitride layers. Journal Physics D: Applied Physics, 2012, 45, 445301.	1.3	50
123	Transfer Printing of Semiconductor Nanowires with Lasing Emission for Controllable Nanophotonic Device Fabrication. ACS Nano, 2016, 10, 3951-3958.	7.3	50
124	Deformation behavior of ion-beam-modified GaN. Applied Physics Letters, 2001, 78, 156-158.	1.5	49
125	Chemical states of nitrogen in ZnO studied by near-edge X-ray absorption fine structure and core-level photoemission spectroscopies. Surface Science, 2006, 600, L81-L85.	0.8	49
126	Dynamics of Strongly Degenerate Electronâ^'Hole Plasmas and Excitons in Single InP Nanowires. Nano Letters, 2007, 7, 3383-3387.	4.5	49

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127	Nanosheets-Based Rhombohedral In₂O₃ 3D Hierarchical Microspheres: Synthesis, Growth Mechanism, and Optical Properties. Journal of Physical Chemistry C, 2009, 113, 10511-10516.	1.5	49
128	Tilted response of fishnet metamaterials at near-infrared optical wavelengths. Physical Review B, 2010, 81, .	1.1	49
129	Emergence of Localized States in Narrow GaAs/AlGaAs Nanowire Quantum Well Tubes. Nano Letters, 2015, 15, 1876-1882.	4.5	49
130	Engineering the Photoresponse of InAs Nanowires. ACS Applied Materials & Interfaces, 2017, 9, 43993-44000.	4.0	49
131	Self-Healing of Fractured GaAs Nanowires. Nano Letters, 2011, 11, 1546-1549.	4.5	48
132	Temperature Dependence of Interband Transitions in Wurtzite InP Nanowires. ACS Nano, 2015, 9, 4277-4287.	7.3	48
133	Manipulating Intermediates at the Auâ€“TiO₂ Interface over InP Nanopillar Array for Photoelectrochemical CO₂ Reduction. ACS Catalysis, 2021, 11, 11416-11428.	5.5	48
134	Bandgap Energy of Wurtzite InAs Nanowires. Nano Letters, 2016, 16, 5197-5203.	4.5	47
135	Wavelength shifting in GaAs quantum well lasers by proton irradiation. Applied Physics Letters, 1997, 71, 2680-2682.	1.5	46
136	Photoluminescence, deep level transient spectroscopy and transmission electron microscopy measurements on MeV self-ion implanted and annealed n-type silicon. Journal of Applied Physics, 2000, 88, 2309-2317.	1.1	46
137	Ion-beam-defect processes in group-III nitrides and ZnO. Vacuum, 2004, 73, 93-104.	1.6	46
138	An ion-implanted InP receiver for polarization resolved terahertz spectroscopy. Optics Express, 2007, 15, 7047.	1.7	46
139	Lasers and photodetectors for mid-infrared 2â€“3â€‚Î¼m applications. Journal of Applied Physics, 2008, 104, 091101.	1.1	46
140	Mechanisms of electrical isolation in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msup><mml:mtext>O</mml:mtext><mml:mo>+</mml:mo></mml:msup></mml:mrow></mml:math> ZnO. Physical Review B, 2008, 78, .	1.1	46
141	Broadband Phase-Sensitive Single InP Nanowire Photoconductive Terahertz Detectors. Nano Letters, 2016, 16, 4925-4931.	4.5	46
142	Effects of rapid thermal annealing on device characteristics of InGaAsâ•GaAs quantum dot infrared photodetectors. Journal of Applied Physics, 2006, 99, 114517.	1.1	45
143	Strengthening Brittle Semiconductor Nanowires through Stacking Faults: Insights from in Situ Mechanical Testing. Nano Letters, 2013, 13, 4369-4373.	4.5	45
144	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. ACS Nano, 2019, 13, 3492-3499.	7.3	45

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145	Dynamic annealing in ion implanted SiC: Flux versus temperature dependence. Journal of Applied Physics, 2003, 94, 7112-7115.	1.1	44
146	Probing valence band structure in wurtzite InP nanowires using excitation spectroscopy. Applied Physics Letters, 2010, 97, 023106.	1.5	44
147	Growth of Straight InAs-on-GaAs Nanowire Heterostructures. Nano Letters, 2011, 11, 3899-3905.	4.5	44
148	Polarized Light Absorption in Wurtzite InP Nanowire Ensembles. Nano Letters, 2015, 15, 998-1005.	4.5	44
149	Influence of Electrical Design on Coreâ€“Shell GaAs Nanowire Array Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 854-864.	1.5	44
150	Determination of Youngâ€™s Modulus of Ultrathin Nanomaterials. Nano Letters, 2015, 15, 5279-5283.	4.5	44
151	Robust Subâ€Monolayers of Co₃O₄ Nanoâ€Islands: A Highly Transparent Morphology for Efficient Water Oxidation Catalysis. Advanced Energy Materials, 2016, 6, 1600697.	10.2	44
152	Review on III-V Semiconductor Single Nanowire-Based Room Temperature Infrared Photodetectors. Materials, 2020, 13, 1400.	1.3	44
153	Passive mode locking of a self-frequency-doubling Yb:YAl_3(BO_3)_4 laser. Optics Letters, 2002, 27, 436.	1.7	43
154	In/sub 0.5/Ga/sub 0.5/As/GaAs quantum dot infrared photodetectors grown by metal-organic chemical vapor deposition. IEEE Electron Device Letters, 2005, 26, 628-630.	2.2	43
155	Formation of Hierarchical InAs Nanoringâ€‰/â€‰GaAs Nanowire Heterostructures. Angewandte Chemie - International Edition, 2009, 48, 780-783.	7.2	43
156	Spatially Resolved Doping Concentration and Nonradiative Lifetime Profiles in Single Si-Doped InP Nanowires Using Photoluminescence Mapping. Nano Letters, 2015, 15, 3017-3023.	4.5	43
157	Identification and modulation of electronic band structures of single-phase Î²-(AlxGa1â^'x)2O3 alloys grown by laser molecular beam epitaxy. Applied Physics Letters, 2018, 113, .	1.5	43
158	Engineering IIIâ€“V Semiconductor Nanowires for Device Applications. Advanced Materials, 2020, 32, e1904359.	11.1	43
159	Hydrogen incorporation, diffusivity and evolution in bulk ZnO. Solid-State Electronics, 2003, 47, 2255-2259.	0.8	42
160	Spontaneous emission of guided polaritons by quantum dot coupled to metallic nanowire: Beyond the dipole approximation. Optics Express, 2009, 17, 17570.	1.7	42
161	Defect-Free GaAs/AlGaAs Coreâ€“Shell Nanowires on Si Substrates. Crystal Growth and Design, 2011, 11, 3109-3114.	1.4	42
162	Long-Lived Hot Carriers in IIIâ€“V Nanowires. Nano Letters, 2016, 16, 3085-3093.	4.5	42

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163	Giant optical pathlength enhancement in plasmonic thin film solar cells using core-shell nanoparticles. Journal Physics D: Applied Physics, 2018, 51, 295106.	1.3	42
164	Ion-implanted InGaAs single quantum well semiconductor saturable absorber mirrors for passive mode-locking. Journal Physics D: Applied Physics, 2001, 34, 2455-2464.	1.3	41
165	Resonant Excitation and Imaging of Nonequilibrium Exciton Spins in Single Coreâ^'Shell GaAsâ^'AlGaAs Nanowires. Nano Letters, 2007, 7, 588-595.	4.5	41
166	Hybrid Highâ€Resolution Threeâ€Dimensional Nanofabrication for Metamaterials and Nanoplasmonics. Advanced Materials, 2013, 25, 1260-1264.	11.1	41
167	Shape Engineering of InP Nanostructures by Selective Area Epitaxy. ACS Nano, 2019, 13, 7261-7269.	7.3	41
168	Effect of irradiation temperature and ion flux on electrical isolation of GaN. Journal of Applied Physics, 2002, 91, 4117-4120.	1.1	40
169	Ion mass effect on vacancy-related deep levels in Si induced by ion implantation. Physical Review B, 2002, 65, .	1.1	40
170	Proton-irradiation-induced intermixing of InGaAs quantum dots. Applied Physics Letters, 2003, 82, 2053-2055.	1.5	40
171	Tailoring GaAs, InAs, and InGaAs Nanowires for Optoelectronic Device Applications. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 766-778.	1.9	40
172	Polarity-driven Nonuniform Composition in InGaAs Nanowires. Nano Letters, 2013, 13, 5085-5089.	4.5	40
173	Antimony Induced {112}A Faceted Triangular GaAs_{1â^'x}Sb_x/InP Core/Shell Nanowires and Their Enhanced Optical Quality. Advanced Functional Materials, 2015, 25, 5300-5308.	7.8	40
174	Review on photonic properties of nanowires for photovoltaics [Invited]. Optics Express, 2016, 24, 17345.	1.7	40
175	Novel impurity-free interdiffusion in GaAs/AlGaAs quantum wells by anodization and rapid thermal annealing. Applied Physics Letters, 1997, 70, 1269-1271.	1.5	39
176	Effects of excitation density on cathodoluminescence from GaN. Applied Physics Letters, 2001, 79, 2154-2156.	1.5	39
177	Structural disorder in ion-implanted AlxGa1â^'xN. Applied Physics Letters, 2002, 80, 787-789.	1.5	39
178	Observation of enhanced defect emission and excitonic quenching from spherically indented ZnO. Applied Physics Letters, 2006, 89, 082102.	1.5	39
179	Observation of blue shifts in ZnO/ZnMgO multiple quantum well structures by ion-implantation induced intermixing. Semiconductor Science and Technology, 2006, 21, L25-L28.	1.0	39
180	Evolution of InAs branches in InAsâ•GaAs nanowire heterostructures. Applied Physics Letters, 2007, 91, 133115.	1.5	39

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181	Three-Dimensional in Situ Photocurrent Mapping for Nanowire Photovoltaics. Nano Letters, 2013, 13, 1405-1409.	4.5	39
182	Anelastic Behavior in GaAs Semiconductor Nanowires. Nano Letters, 2013, 13, 3169-3172.	4.5	39
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